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Infrared Applications of Semiconductors II

Editors: Donald L. McDaniel, M. Omar Manasreh, Richard H. Miles and Sivalingam Sivananthan

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Infrared Applications of Semiconductors II

Editors: Donald L. McDaniel, M. Omar Manasreh, Richard H. Miles and Sivalingam Sivananthan

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PREFACE

The symposium titled "Infrared Applications of Semiconductors II" was held as Symposium F of the 1997 MRS Fall Meeting in Boston, Massachusetts. The sessions filled the four days of December 1–4. This very successful symposium was the second annual event covering this subject area, establishing the symposium topic as a regular part of the annual Fall Meeting. The session covered recent progress in III-V and II-VI interband and intersubband transitions in semiconductor materials and devices, and in semiconductor nonlinear optical and OPO materials. Participation was truly international featuring participants from five continents. A total of 74 papers and 59 posters were presented, most of which are detailed in this volume. These presentations chronicle the extensive progress being made in the modeling, design, fabrication and characterization of a diverse array of infrared semiconductor structures.

Donald L. McDaniel, Jr.
M. Omar Manasreh
Richard H. Miles
Sivalingam Sivananthan

January 1998

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Air Force Office of Scientific Research (AFOSR)

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Air Force Research Laboratory
Space Sensing and Vehicle Control Branch (AFRL/VSSS)

In addition, we wish to thank the invited speakers for setting the tone of the sessions, the session chairs for assistance in organizing and managing their sessions, the many people who assisted in refereeing the papers in this volume and the staff of Materials Research Society. Neither the symposium nor this volume would have been possible without the selfless participation of these people.

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